

# 2SC3692

Silicon NPN Transistors

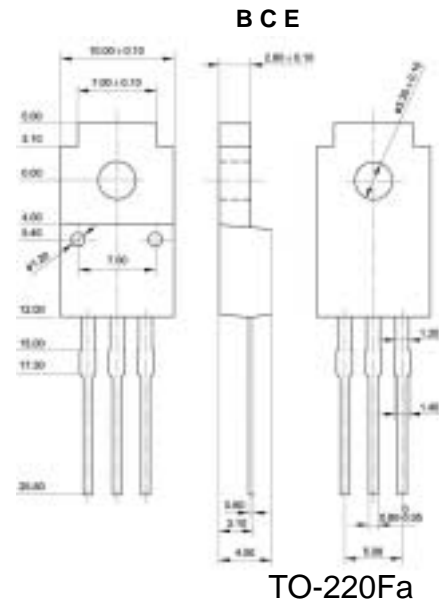


## ◆ Features

- . With TO-220Fa package
- . High speed ,power switching applications

## ◆ Absolute Maximum Ratings Tc=25

SYMBOL	PARAMETER	RATING	UNIT
$V_{CBO}$	Collector to base voltage	100	V
$V_{CEO}$	Collector to emitter voltage	60	V
$V_{EBO}$	Emitter to base voltage	5	V
$I_C$	Collector current	7	A
$P_C$	Collector power dissipation	30	W
$T_j$	Junction temperature	150	
$T_{stg}$	Storage temperature	-55~150	



## ◆ Electrical Characteristics Tc=25

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ.	MAX	UNIT
$I_{CBO}$	Collector cut-off current	$V_{CB}=60V; I_E=0$			10	uA
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5V; I_C=0$			10	uA
$I_{CEO}$	Collector cut-off current					
$V_{CBO}$	Collector-base breakdown voltage					
$V_{CEO(SUS)}$	Collector-emitter Sustaining voltage	$I_C=30mA; I_B=0$	60			V
$V_{EBO}$	Emitter-base breakdown voltage					
$V_{CE(sat)1}$	Collector-emitter saturation voltages	$I_C=6A; I_B=0.3A$			0.5	V
$V_{CE(sat)2}$	Collector-emitter saturation voltages					
$h_{FE-1}$	Forward current transfer ratio	$I_C=1.5A; V_{CE}=2V$	100		400	
$h_{FE-2}$	Forward current transfer ratio					
$V_{BE(sat)1}$	Base-emitter saturation voltages	$I_C=6A; I_B=0.3A$			1.5	V
$V_{BE(sat)2}$	Base-emitter saturation voltages					
$f_T$	Transition frequency	$I_C=1A; V_{CE}=10V$		150		MHz
$C_{ob}$	Collector Out put Capacitance	$I_C=0, V_{CB}=10V f=1MHz$		100		pF